March 2015



# FGH40N60UF 600 V, 40 A Field Stop IGBT

## Features

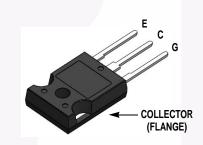
- High Current Capability
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.8 V @ I<sub>C</sub> = 40 A
- High Input Impedance
- Fast Switching
- RoHS Compliant

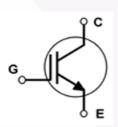
# Applications

Solar Inverter, UPS, Welder, PFC

# **General Description**

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





# **Absolute Maximum Ratings**

Symbol	Description	Ratings	Unit	
V <sub>CES</sub>	Collector to Emitter Voltage		600	V
V <sub>GES</sub>	Gate to Emitter Voltage		±20	V
	Transient Gate-to-Emitter Voltage	±30	v	
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	80	A
	Collector Current	@ T <sub>C</sub> = 100°C	40	А
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	120	A
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	290	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100 <sup>o</sup> C	116	W
Т <sub>Ј</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C	

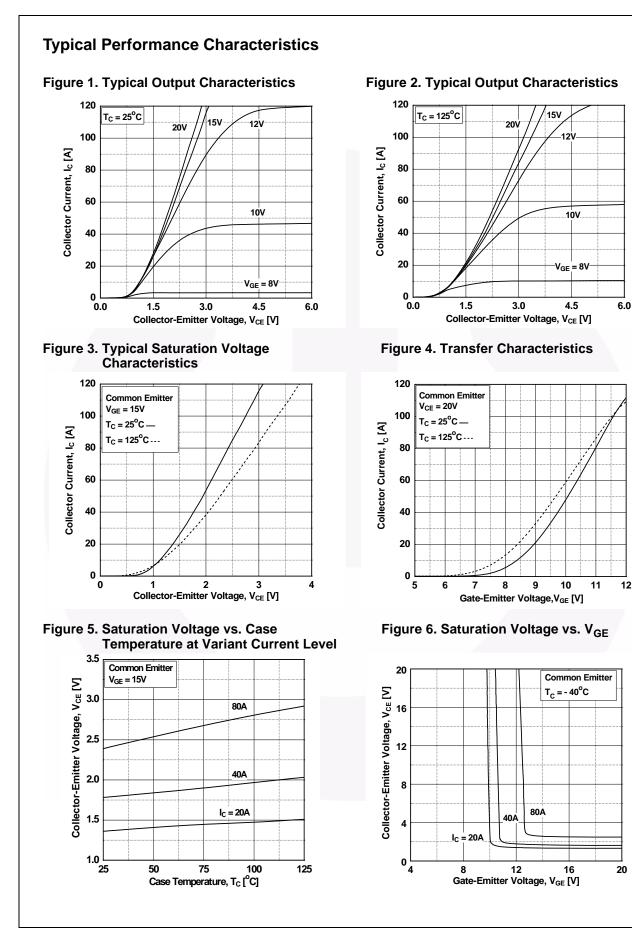
Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.43	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Part Nu	mber	Top Mark	Package	Packing Method	Reel Size	Tape Wid	th Q	Quantity	
FGH40N6	GH40N60UFTU FGH40N60UF TO-247		Tube	N/A	N/A		30		
Electric	al Cha	aracteristics	s of the IC	<b>GBT</b> $T_{C} = 25^{\circ}C$ unless other	wise noted				
Symbol		Paramete	r	Test Conditio	ns Min	. Тур.	Max.	Unit	
Off Charac	toristics				ł			!	
BV <sub>CES</sub>			hown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 250 μA	600	-	-	V	
$\Delta BV_{CES}$ /	Temper	Collector to Emitter Breakdown Voltage remperature Coefficient of Breakdown		$V_{GE} = 0 V, I_C = 250 \mu A$ $V_{GE} = 0 V, I_C = 250 \mu A$	-	0.6	_	V/°C	
ΔT <sub>J</sub>	Voltage	•					050		
I <sub>CES</sub>		or Cut-Off Current		$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μA	
I <sub>GES</sub>	G-E Le	akage Current	_	$V_{GE} = V_{GES}, V_{CE} = 0 V$	·	-	±400	nA	
On Charac	teristics								
V <sub>GE(th)</sub>	G-E Th	reshold Voltage		I <sub>C</sub> = 250 μA, V <sub>CE</sub> = V <sub>GE</sub>	4.0	5.0	6.5	V	
. ,		Collector to Emitter Saturation Voltage		I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	-	1.8	2.4	V	
V <sub>CE(sat)</sub>	Collecto			$I_{C} = 40 \text{ A}, V_{GE} = 15 \text{ V},$ $T_{C} = 125^{\circ}\text{C}$	-	2.0	-	V	
				-					
Dynamic C									
C <sub>ies</sub>		apacitance		V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz	-	2110	-	pF	
C <sub>oes</sub>	· ·	Capacitance			-	200	-	pF	
C <sub>res</sub>	Revers	Reverse Transfer Capacitance			-	60	-	pF	
Switching	Characte	eristics							
t <sub>d(on)</sub>	1	n Delay Time	-		-	24	-	ns	
t <sub>r</sub>	Rise Tir				_	44	-	ns	
t <sub>d(off)</sub>	Turn-O	ff Delay Time		V <sub>CC</sub> = 400 V, I <sub>C</sub> = 40 A,	-	112	-	ns	
t <sub>f</sub>	Fall Tim			$R_{G} = 10 \Omega, V_{GE} = 15 V,$	-	30	60	ns	
E <sub>on</sub>	Turn-O	n Switching Loss		Inductive Load, T <sub>C</sub> = 25 <sup>c</sup>	°C - 0°	1.19	-	mJ	
E <sub>off</sub>		ff Switching Loss			-	0.46	-	mJ	
E <sub>ts</sub>	Total S	witching Loss			-	1.65	-	mJ	
t <sub>d(on)</sub>		n Delay Time			-	24	-	ns	
t <sub>r</sub>	Rise Tir			+	-	45	-	ns	
t <sub>d(off)</sub>	Turn-O	ff Delay Time		V <sub>CC</sub> = 400 V, I <sub>C</sub> = 40 A, R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V,	-	120	-	ns	
t <sub>f</sub>	Fall Tim	ne			-	40		ns	
E <sub>on</sub>	Turn-O	n Switching Loss		Inductive Load, T <sub>C</sub> = 125	5°C -	1.2	- /	mJ	
E <sub>off</sub>		ff Switching Loss		1	-	0.69	- (	mJ	
E <sub>ts</sub>	Total Sv	witching Loss		+	-	1.89		mJ	
Qg	Total G	ate Charge			-	120		nC	
-				V <sub>CE</sub> = 400 V, I <sub>C</sub> = 40 A,				-	
Q <sub>ge</sub>	Gate to	Emitter Charge		$V_{GE} = 15 V$	-	14	-	nC	



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# Typical Performance Characteristics Figure 7. Saturation Voltage vs. V<sub>GE</sub> 20

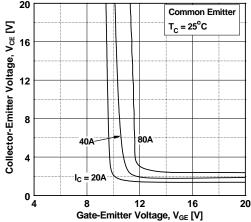
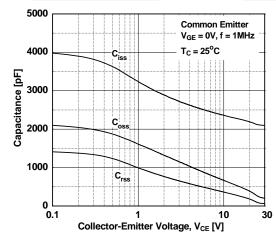


Figure 9. Capacitance Characteristics





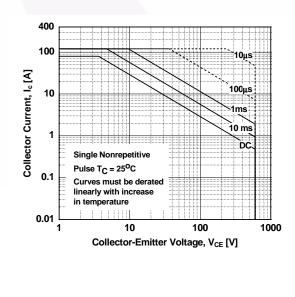


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

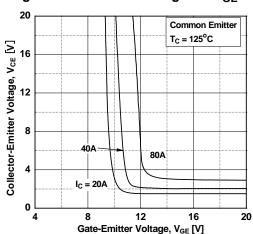


Figure 10. Gate charge Characteristics

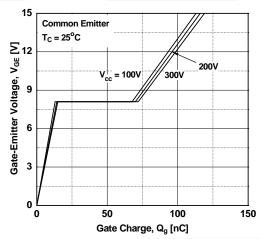
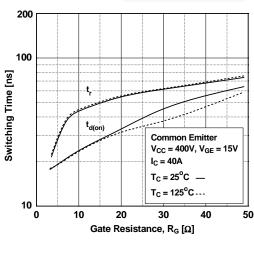


Figure 12. Turn-on Characteristics vs. Gate Resistance



FGH40N60UF — 600 V, 40 A Field Stop IGBT

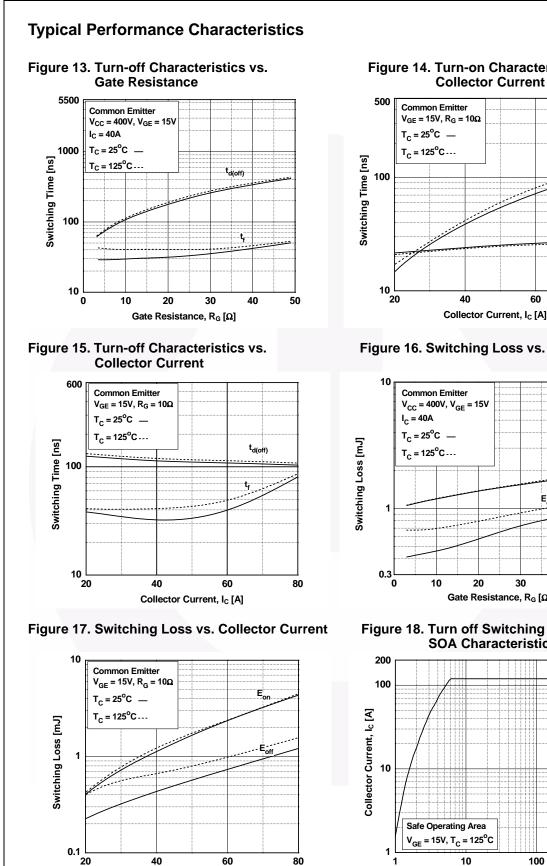


Figure 14. Turn-on Characteristics vs. **Collector Current** 

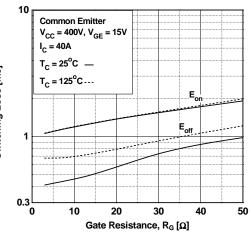
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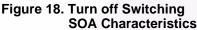
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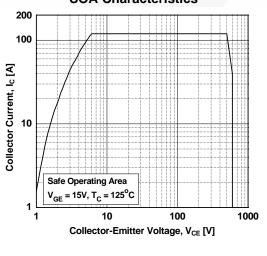
80



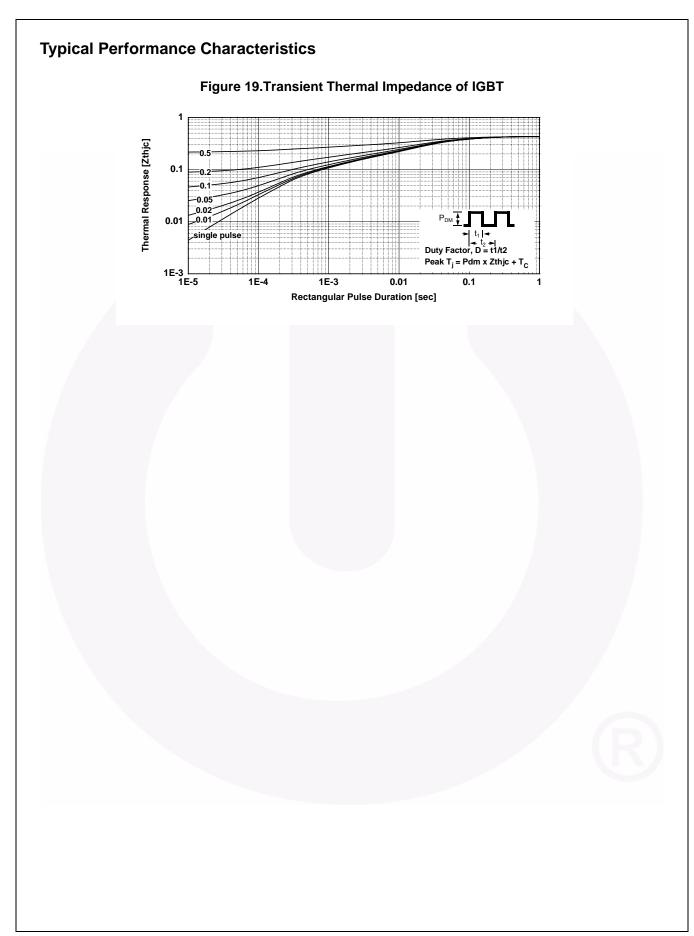
60

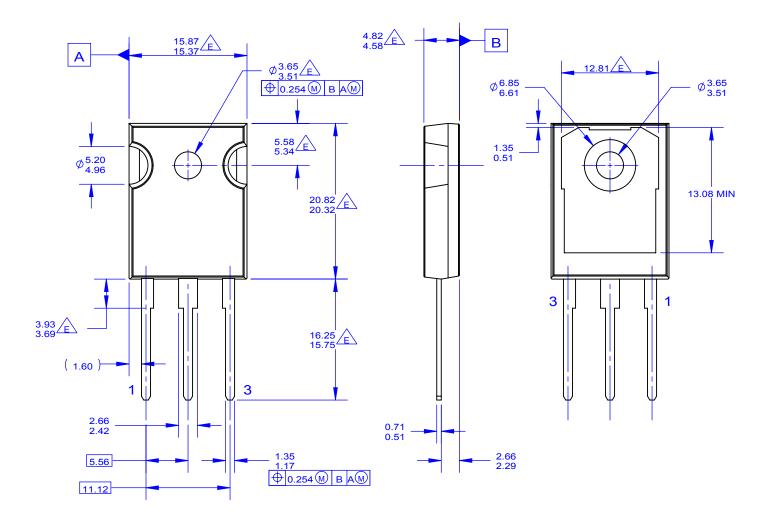






Collector Current, Ic [A]





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